

Conced
E1
cont.⁵
D3

a semiconductor substrate;
an interlayer insulating film located on the semiconductor substrate;
wirings located on the interlayer insulating film; and
a passivation film covering the surface of the interlayer insulating film and the wirings, including a first insulating film that is a modified spin-on-glass (SOG) film formed by implanting boron impurity into an organic SOG film.

sub
E3
DH
5

31. A semiconductor device comprising:
a semiconductor substrate;
an interlayer insulating film located on the semiconductor substrate;
wirings located on the interlayer insulating film; and
a passivation film covering the surface of the interlayer insulating film and the wirings, including a first insulating film that is a modified spin-on-glass (SOG) film formed by implanting boron impurity into an inorganic SOG film.
